

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.5	2	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=4.5\text{A}$		39	50	m Ω
		$T_J=125^{\circ}\text{C}$		63	78	
		$V_{GS}=4.5\text{V}$, $I_D=3\text{A}$		50	68	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=4.5\text{A}$		10		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.79	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		200		pF
C_{oss}	Output Capacitance			35		pF
C_{rss}	Reverse Transfer Capacitance			25		pF
R_g	Gate resistance	$f=1\text{MHz}$	1	2	3	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=4.5\text{A}$		4.05	10	nC
$Q_g(4.5\text{V})$	Total Gate Charge			2	6	nC
Q_{gs}	Gate Source Charge			0.55		nC
Q_{gd}	Gate Drain Charge			1		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=3.3\Omega$, $R_{GEN}=3\Omega$		4.5		ns
t_r	Turn-On Rise Time			1.5		ns
$t_{D(off)}$	Turn-Off DelayTime			18.5		ns
t_f	Turn-Off Fall Time			15.5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=4.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		7.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=4.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		2.5		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^{\circ}\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

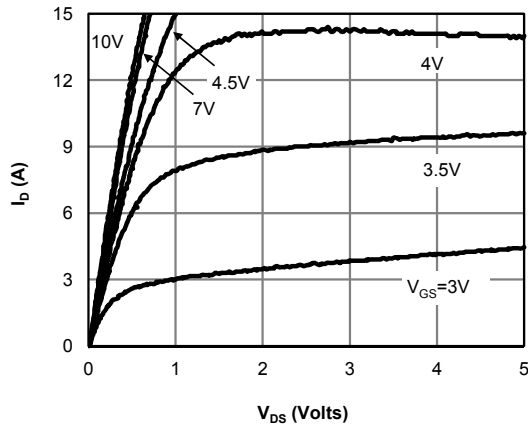


Figure 1: On-Region Characteristics (Note E)

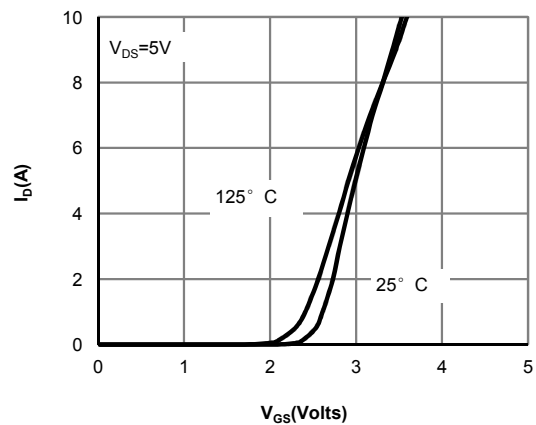


Figure 2: Transfer Characteristics (Note E)

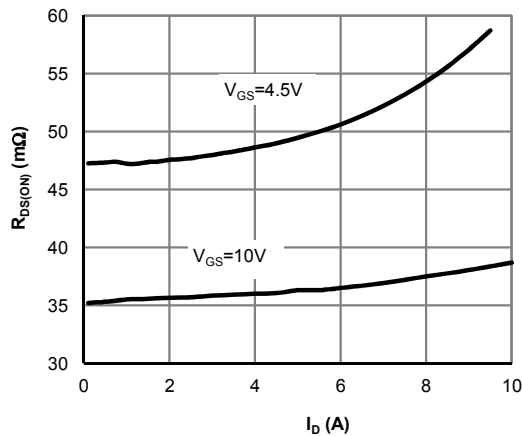


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

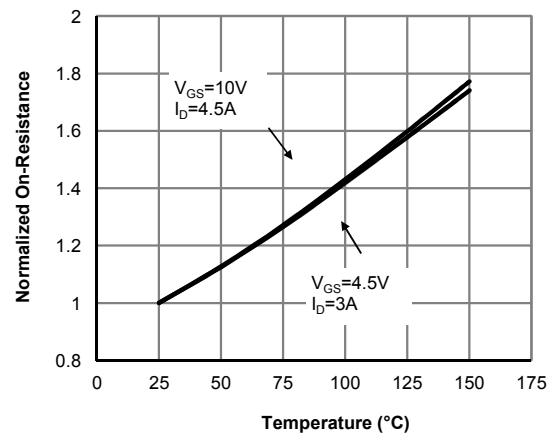


Figure 4: On-Resistance vs. Junction Temperature (Note E)

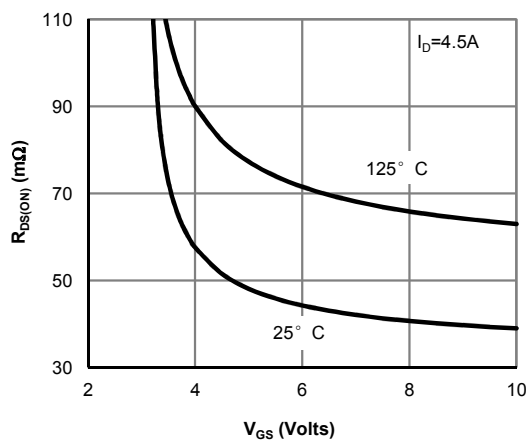


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

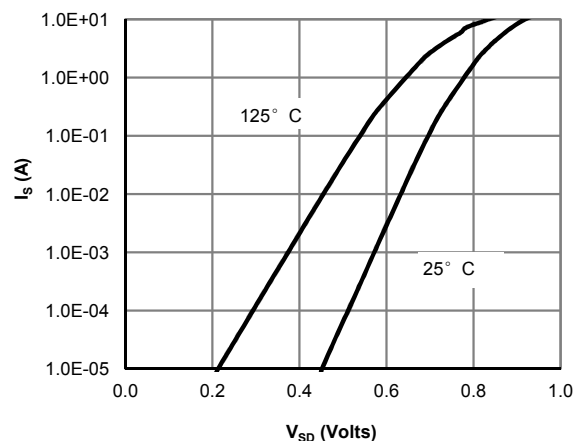


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

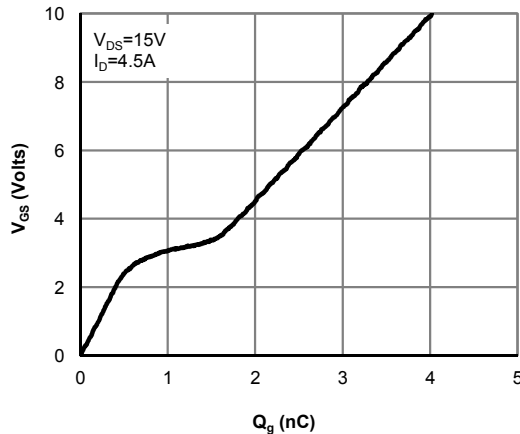


Figure 7: Gate-Charge Characteristics

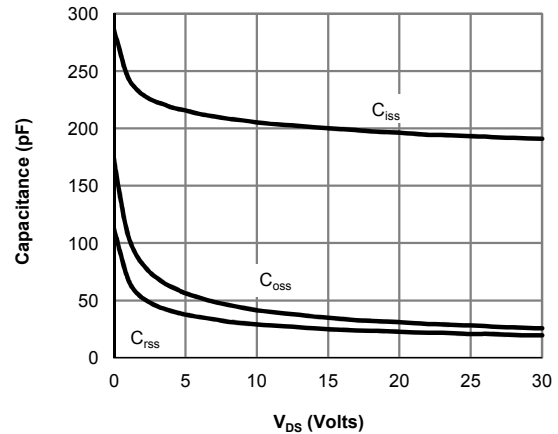


Figure 8: Capacitance Characteristics

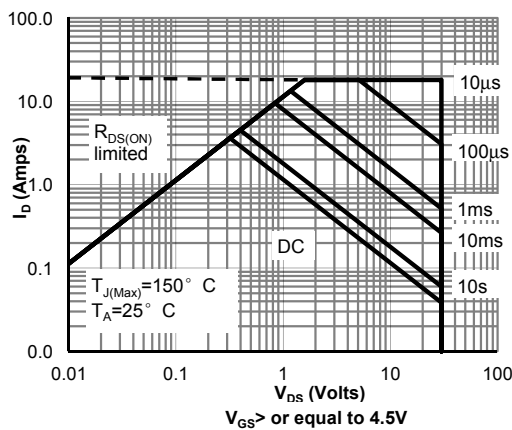


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

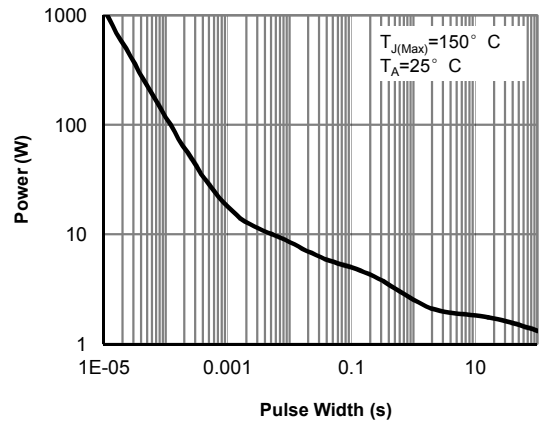


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

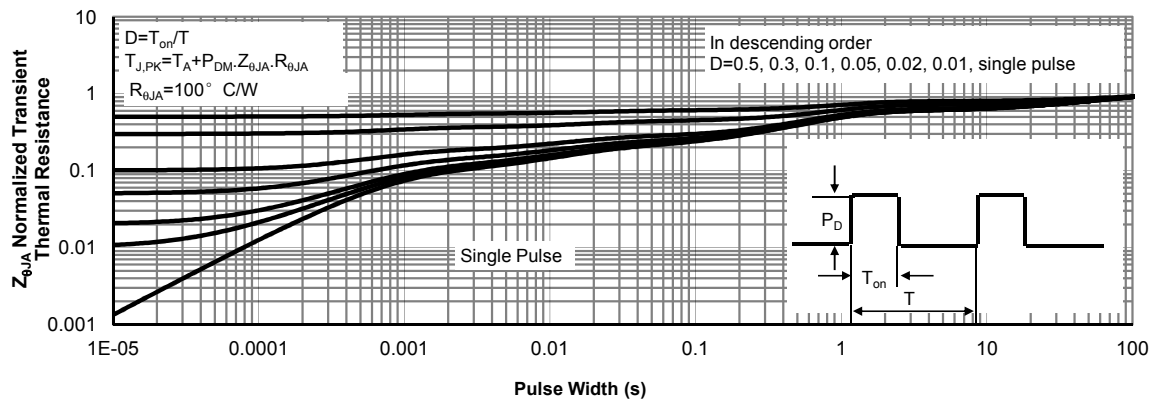
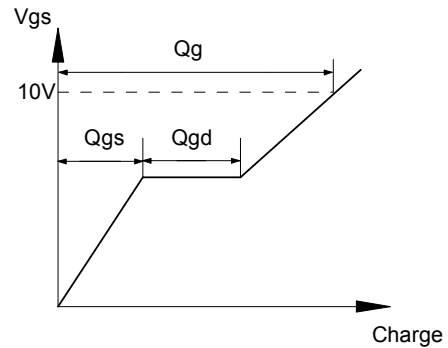
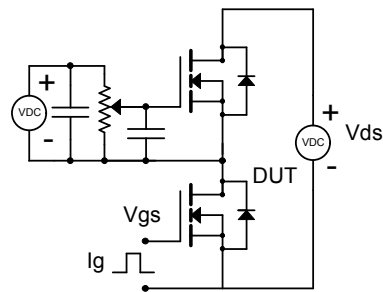
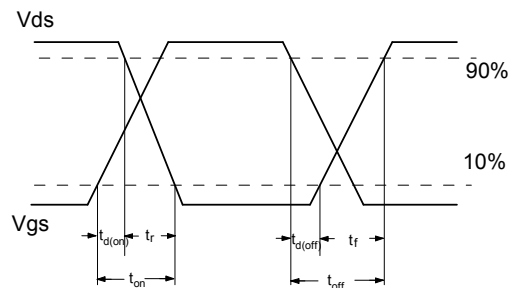
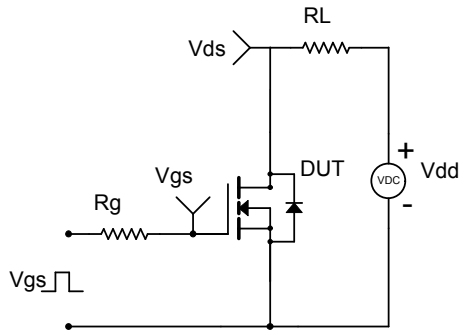


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

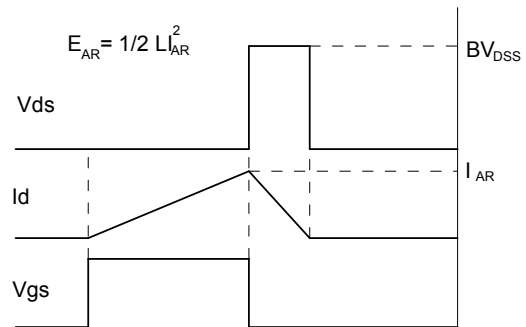
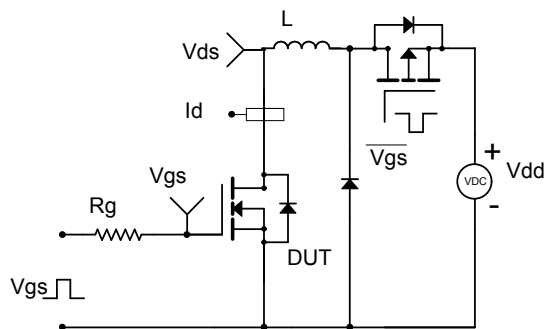
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

